Unit in mm

#### TOSHIBA PHOTOCOUPLER GaAlAs IRED + PHOTO-IC

## **TLP719**

Digital logic ground isolation

Line receivers

Microprocessor system interfaces

Switching power supply feedback control

Transistor invertors

The TOSHIBA TLP719 consists of a GaAlAs high-output light-emitting diode and a high-speed detector.

This unit is a 6-lead SDIP. The TLP719 is 50% smaller than the 8-pin DIP and meets the reinforced insulation class requirements of international safety standards. Therefore the mounting area can be reduced in equipment requiring safety standard certification.

The TLP719 has a Faraday shield integrated on the photodetector chip to provide an effective common mode noise transient immunity. Therefore this product is suitable for application in noisy environmental conditions.

· Open collector

Package type : SDIP6

• Isolation voltage : 5000 Vrms (min)

Common mode transient immunity : ±10 kV/us(min) @V<sub>CM</sub> = 400 V

Switching speed :  $t_{pHL}/t_{pLH} = 0.8 \mu s$  (max)

@  $I_F = 16 \text{ mA}$ ,  $V_{CC} = 5 \text{ V}$ ,  $R_L = 1.9 \text{ k}\Omega$ ,  $Ta = 25 ^{\circ}\text{C}$ 

· TTL compatible

Construction mechanical rating

	7.62-mm pitch standard type	10.16-mm pitch TLPXXXF type
Creepage Distance	7.0 mm (min)	8.0 mm (min)
Clearance	7.0 mm (min)	8.0 mm (min)
Insulation Thickness	0.4 mm (min)	0.4 mm (min)

UL recognized : UL1577, File No. E67349

• Option (D4)

TÜV approved : EN60747-5-2

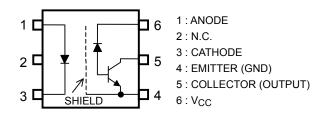
Certificate No. R50033433

Maximum operating insulation voltage: 890 Vpk Highest permissible over voltage: 8000 Vpk

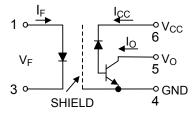
( Note ) When a EN60747-5-2 approved type is needed, please designate the "Option(D4)"

# 4.58±0.25 6 5 4 9 7.62±0.25 1 2 3 9 9 9 7.62±0.25 1.27±0.2 1.25±0.25 9.7±0.3 11-5J1 TOSHIBA 11-5J1 Weight: 0.26 g (typ.)

#### **PIN CONFIGURATION (Top View)**



#### **SCHEMATIC**



A 0.1- $\mu$ F bypass capacitor must be connected between pins 4 and 6. (See Note 7.)



#### Absolute Maximum Ratings (Ta = 25 °C)

	Characteristic		Symbol	Rating	Unit
	Forward current	(Note 1)	l <sub>F</sub>	25	mA
	Pulse forward current	(Note 2)	I <sub>FP</sub>	50	mA
LED	Peak transient forward current	(Note 3)	I <sub>FPT</sub>	1	Α
	Reverse voltage		V <sub>R</sub>	5	V
	Diode power dissipation	(Note 4)	PD	45	mW
	Junction temperature		Тј	125	°C
	Output current		IO	8	mA
	Peak output current		I <sub>OP</sub>	16	mA
Detector	Output voltage		Vo	-0.5~20	V
Dete	Supply voltage		V <sub>CC</sub>	-0.5~30	V
	Output power dissipation	(Note 5)	Po	100	mW
	Junction Temperature		Тј	125	°C
Ope	rating temperature range		T <sub>opr</sub>	-55~100	°C
Stor	Storage temperature range		T <sub>stg</sub>	-55~125	°C
Lea	d soldering temperature (10 s)		T <sub>sol</sub>	260	°C
Isola	ation voltage (AC, 1 minute, R.H.≤ 60 %)	(Note 6)	BVS	5000	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Derate 0.45 mA / °C above 70 °C.
- Note 2: 50% duty cycle, 1 ms pulse width.

  Derate 0.9 mA / °C above 70 °C.
- Note 3: Pulse width  $\leq 1 \mu s$ , 300 pps.
- Note 4: Derate 0.8 mW / °C above 70 °C.
- Note 5: Derate 1.8 mW / °C above 70 °C.
- Note 6: Device considered a two-terminal device: pins 1, 2 and 3 paired with pins 4, 5 and 6 respectively.
- Note 7: A ceramic capacitor  $(0.1 \, \mu F)$  should be connected from pin 6 to pin 4 to stabilize the operation of the high-gain linear amplifier. Failure to provide the bypassing may impair the switching property. The total lead length between capacitor and coupler should not exceed 1 cm.



## Electrical Characteristics (Ta = 25 °C)

	Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
	Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 16 mA		1.65	1.85	V
ED	Forward voltage Temperature coefficient	ΔV <sub>F</sub> / ΔTa	I <sub>F</sub> = 16 mA	_	-2	-	mV / °C
-	Reverse current	I <sub>R</sub>	V <sub>R</sub> = 5 V	_	_	10	μΑ
	Capacitance between terminals	C <sub>T</sub>	V <sub>F</sub> = 0 V , f = 1 MHz	_	45	_	pF
Detector	HIGH-level output current	I <sub>OH</sub> (1)	$I_F = 0 \text{ mA}, V_{CC} = V_O = 5.5 \text{ V}$	_	3	500	nA
		I <sub>OH</sub> (2)	$I_F = 0 \text{ mA}, V_{CC} = 30 \text{ V}$ $V_O = 20 \text{ V}$	_	_	5	
		Іон	$I_F = 0 \text{ mA }, V_{CC} = 30 \text{ V}$ $V_O = 20 \text{ V}, Ta = 70 ^{\circ}\text{C}$	_	_	50	μΑ
	HIGH-level supply current	Іссн	I <sub>F</sub> = 0 mA ,V <sub>CC</sub> = 30 V	_	0.01	1	μA
	Supply voltage	V <sub>CC</sub>	I <sub>CC</sub> = 0.01 mA	30	_	_	V
	Output voltage	V <sub>O</sub>	I <sub>O</sub> = 0.5 mA	20	_	_	V

## Coupled Electrical Characteristics (Ta = 25 °C)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Current transfer ratio		$I_F = 16 \text{ mA}, V_{CC} = 4.5 \text{ V}$ $V_O = 0.4 \text{ V}$	20	1	_	%
LOW-level output voltage	V <sub>OL</sub>	$I_F = 16 \text{ mA}, V_{CC} = 4.5 \text{ V}$ $I_O = 2.4 \text{ mA}$	ı	ı	0.4	V

### **Isolation Characteristics (Ta = 25 °C)**

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Capacitance input to output	CS	V = 0 V , f = 1 MHz (Note 6)	_	0.8	_	pF
Isolation resistance	R <sub>S</sub>	R.H. ≤ 60% ,V <sub>S</sub> = 500 V (Note 6)	1×10 <sup>12</sup>	10 <sup>14</sup>	ı	Ω
Isolation voltage	BVS	AC, 1 minute	5000	_	1	V
		AC, 1 second , in oil	_	10000	1	V <sub>rms</sub>
		DC, 1 minute , in oil	_	10000		Vdc

Characteristic	Symbol	Test Cir- cuit	Test Condition	Min.	Тур.	Max.	Unit
Propagation delay time $(H \rightarrow L)$	t <sub>pHL</sub>	- Fig1	$I_F = 0 \rightarrow 16 \text{ mA}$ $R_L = 1.9 \text{k}\Omega$	_	ı	0.8	μs
Propagation delay time $(L \rightarrow H)$	t <sub>pLH</sub>		$I_F = 16 \rightarrow 0 \text{ mA}$ $R_L = 1.9 \text{k}\Omega$	_	_	0.8	μs
Common mode transient immunity at logic HIGH output (Note 8)	CM <sub>H</sub>	- Fig2	$I_F = 0 \text{ mA}$ $V_{CM} = 400 \text{ Vp-p}$ $R_L = 1.9 \text{k}\Omega$	10000	ı	ı	V / µs
Common mode transient immunity at logic LOW output (Note 8)	CML		$I_F = 16 \text{ mA}$ $V_{CM} = 400 \text{ Vp-p}$ $R_L = 1.9 \text{ k}\Omega$	-10000	ı	-	V / µs

Note 8 :  $CM_L$  is the maximum rate of fall of the common mode voltage that can be sustained with the output voltage in the logic LOW state ( $V_O < 0.8 \text{ V}$ ).

 $CM_H$  is the maximum rate of rise of the common mode voltage that can be sustained with the output voltage in the logic HIGH state ( $V_O > 2 V$ ).

Figure 1. Switching Time Test Circuit

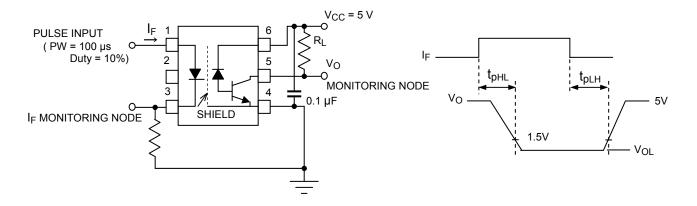
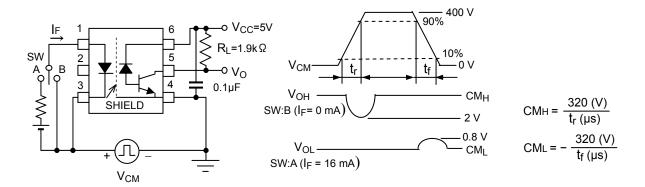
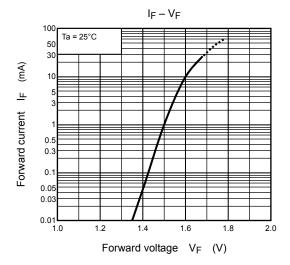
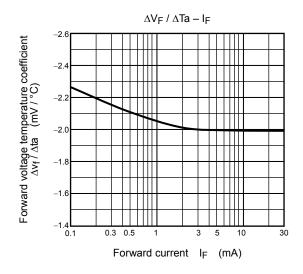
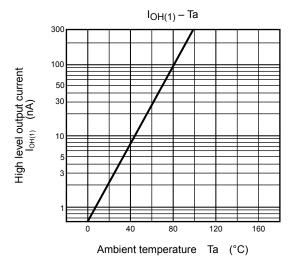


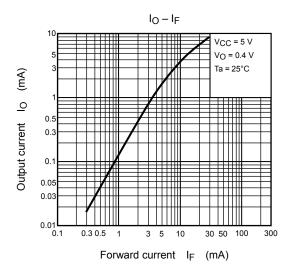
Figure 2. Common Mode Noise Immunity Test Circuit.

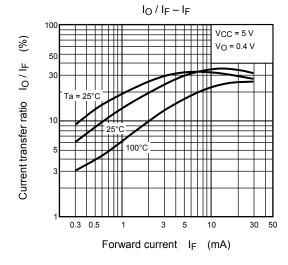


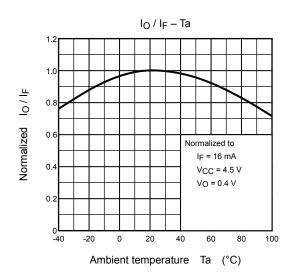


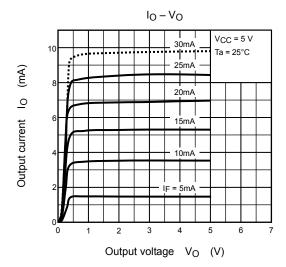


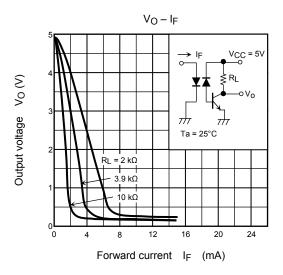


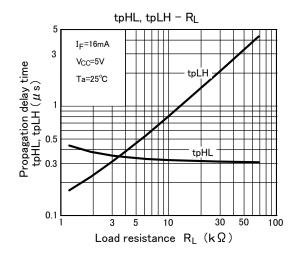


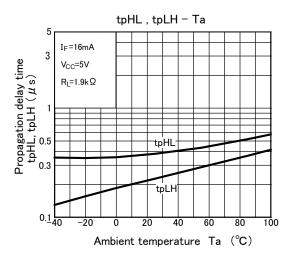












#### **RESTRICTIONS ON PRODUCT USE**

20070701-EN

- The information contained herein is subject to change without notice.
- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.
  In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc.
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in his document shall be made at the customer's own risk.
- The products described in this document shall not be used or embedded to any downstream products of which manufacture, use and/or sale are prohibited under any applicable laws and regulations.
- The information contained herein is presented only as a guide for the applications of our products. No
  responsibility is assumed by TOSHIBA for any infringements of patents or other rights of the third parties which
  may result from its use. No license is granted by implication or otherwise under any patents or other rights of
  TOSHIBA or the third parties.
- GaAs(Gallium Arsenide) is used in this product. The dust or vapor is harmful to the human body. Do not break, cut, crush or dissolve chemically.
- Please contact your sales representative for product-by-product details in this document regarding RoHS
  compatibility. Please use these products in this document in compliance with all applicable laws and regulations
  that regulate the inclusion or use of controlled substances. Toshiba assumes no liability for damage or losses
  occurring as a result of noncompliance with applicable laws and regulations.